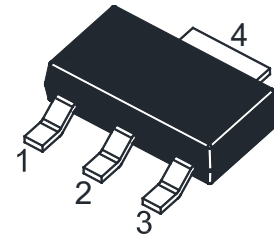


## PNP Silicon Epitaxial Planar Power Transistor

### Features

- AEC-Q101 Qualified
- Halogen and Antimony Free(HAF), RoHS compliant



1.Base 2.Collector 3.Emitter 4. Collector  
SOT-223 Plastic Package

### Applications

- Low-side switches
- Power management
- Battery-driven devices

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	100	V
Collector Emitter Voltage	$-V_{CE0}$	80	V
Emitter Base Voltage	$-V_{EB0}$	5	V
Collector Current	$-I_C$	1	A
Peak Collector Current	$-I_{CM}$	1.5	A
Peak Base Current	$-I_{BM}$	0.2	A
Total Power Dissipation <sup>1)</sup>	$P_{tot}$	1.3	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient <sup>1)</sup>	$R_{\theta JA}$	96	$^\circ\text{C/W}$

<sup>1)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

## Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 2\text{ V}$ , $-I_C = 5\text{ mA}$	$h_{FE}$	40	-	-	-
at $-V_{CE} = 2\text{ V}$ , $-I_C = 500\text{ mA}$	$h_{FE}$	25	-	-	-
at $-V_{CE} = 2\text{ V}$ , $-I_C = 150\text{ mA}$	$h_{FE}$	63	-	160	-
	$h_{FE}$	100	-	250	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	100	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	80	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Base Emitter Voltage at $-V_{CE} = 2\text{ V}$ , $-I_C = 500\text{ mA}$	$-V_{BE(on)}$	-	-	1	V
Transition Frequency at $-V_{CE} = 10\text{ V}$ , $-I_C = 50\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	-	125	-	MHz

## Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

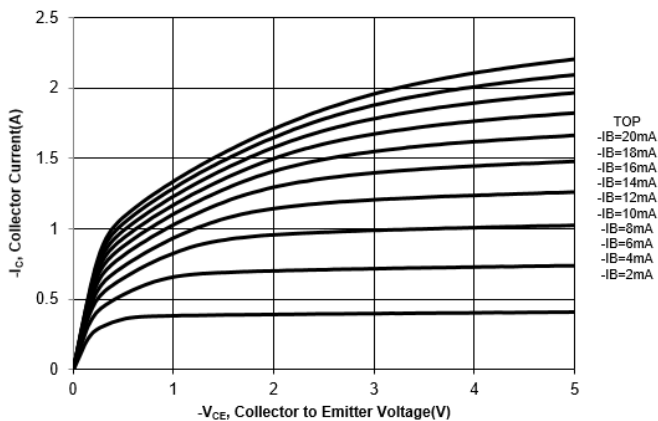


Fig. 2 Collector Current vs. Base to Emitter Voltage

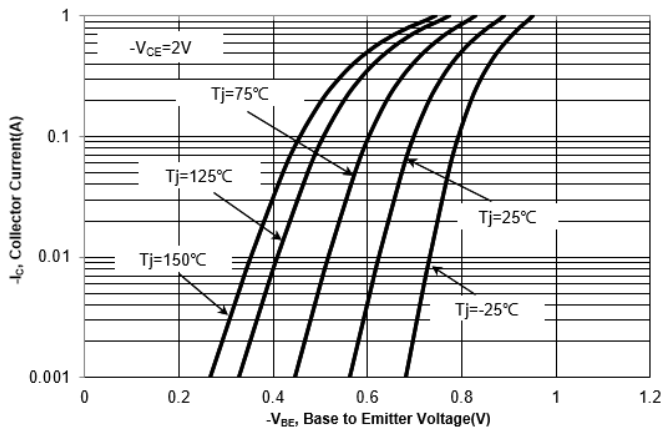


Fig. 3 DC Current Gain vs. Collector Current

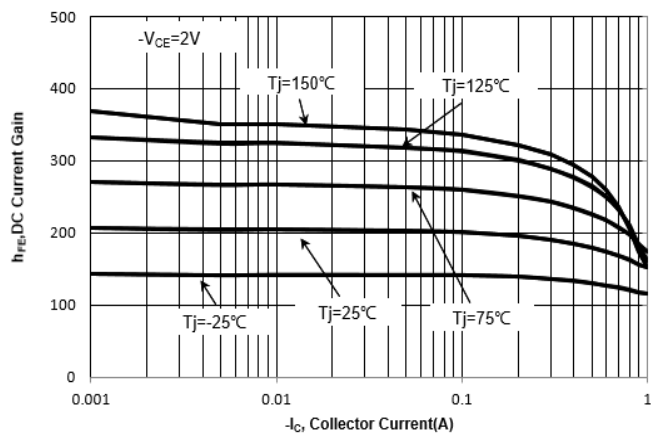
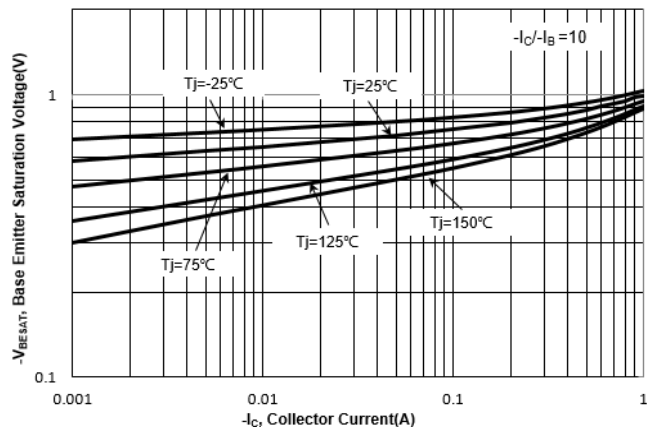


Fig. 4  $V_{BESAT}$  vs. Collector Current



## Electrical Characteristics Curves

Fig. 5  $V_{CESAT}$  vs. Collector Current

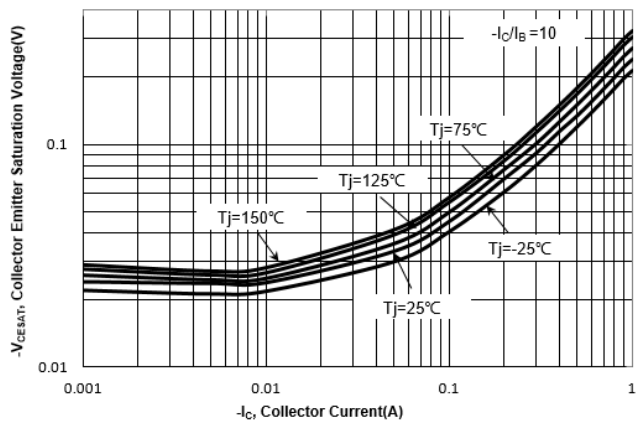


Fig. 6 Output Capacitance

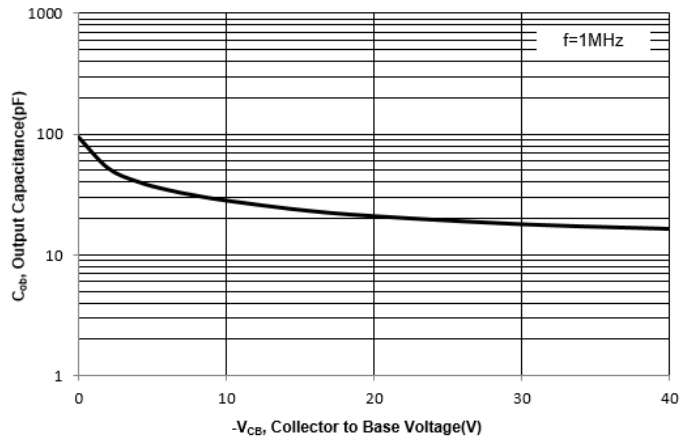
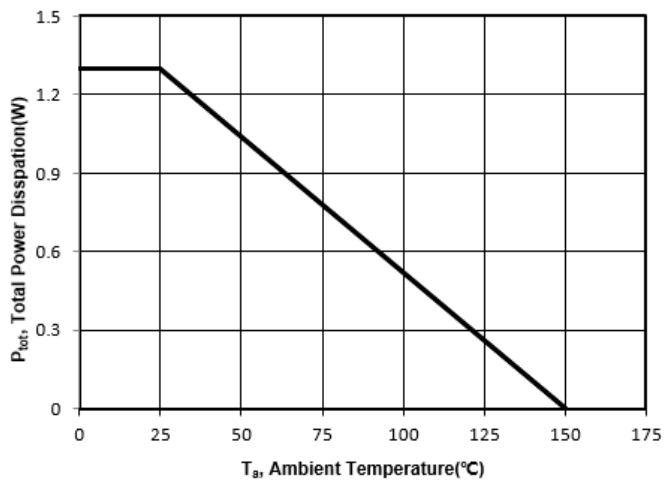
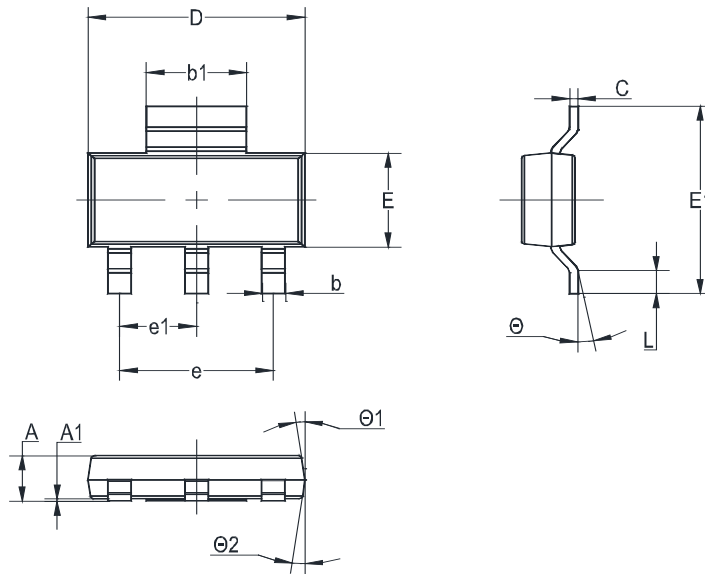


Fig. 7 Power Derating Curve



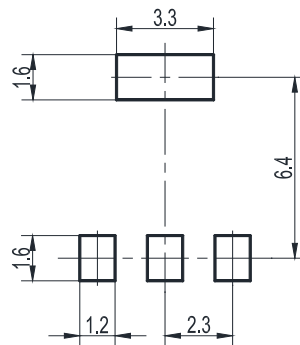
## Package Outline (Dimensions in mm)

SOT-223



Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	θ	θ1	θ2
mm	1.8	0.1	0.8	3.1	0.32	6.7	3.7	7.3	4.6	2.3	1.1	10°	7°	7°
	1.5	MAX	0.6	2.9	0.22	6.3	3.3	6.7	TYP	TYP	0.7	0°	0°	0°

## Recommended Soldering Footprint



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

## Marking information

" BCP53-\*Q " = Part No. ("\*" = HFE grouping Code)

" \*\*\*\* " = Date Code Marking

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